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[ON Semiconductor](#)
[NTMD4184PFR2G](#)

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NTMD4184PF

Power MOSFET and Schottky Diode

-30 V, -4.0 A, Single P-Channel with 20 V, 2.2 A, Schottky Barrier Diode

Features

- FETKY™ Surface Mount Package Saves Board Space
- Independent Pin-Out for MOSFET and Schottky Allowing for Design Flexibility
- Low $R_{DS(on)}$ MOSFET and Low V_F Schottky to Minimize Conduction Losses
- Optimized Gate Charge to Minimize Switching Losses
- This is a Pb-Free Device

Applications

- Disk Drives
- DC-DC Converters
- Printers

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	$T_A = 25^\circ\text{C}$	-3.3
		$T_A = 70^\circ\text{C}$	-2.6
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	$T_A = 25^\circ\text{C}$	1.6
		$T_A = 70^\circ\text{C}$	-
Continuous Drain Current $R_{\theta JA}$ (Note 2)	I_D	$T_A = 25^\circ\text{C}$	-2.3
		$T_A = 70^\circ\text{C}$	-1.8
Power Dissipation $R_{\theta JA}$ (Note 2)	P_D	$T_A = 25^\circ\text{C}$	0.77
		$T_A = 70^\circ\text{C}$	-
Continuous Drain Current $R_{\theta JA} t < 10$ s (Note 1)	I_D	$T_A = 25^\circ\text{C}$	-4.0
		$T_A = 70^\circ\text{C}$	-3.2
Power Dissipation $R_{\theta JA} t < 10$ s (Note 1)	P_D	2.31	W
Pulsed Drain Current	I_{DM}	-10	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	-1.3	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

SCHOTTKY MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R	20	V
Average Rectified Forward Current, (Note 1)	I_F	Steady State	2.2
		$t < 10$ s	3.2



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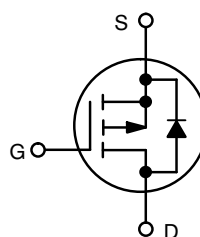
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P-CHANNEL MOSFET

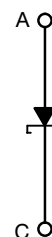
$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
-30 V	95 m Ω @ -10 V	-4.0 A
	165 m Ω @ -4.5 V	

SCHOTTKY DIODE

V_R Max	V_F Max	I_F Max
20 V	0.58 V	2.2 A

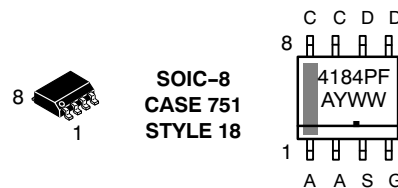


P-Channel MOSFET



Schottky Diode

MARKING DIAGRAM & PIN ASSIGNMENT



4184PF = Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTMD4184PFR2G	SOIC-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter MOSFET & Schottky	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	79	°C/W
Junction-to-Ambient – $t \leq 10$ s Steady State (Note 1)	$R_{\theta JA}$	54	
Junction-to-FOOT (Drain) Equivalent to $R_{\theta JC}$	$R_{\theta JF}$	50	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	163	

- Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			30		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}$	$T_J = 25^\circ\text{C}$		-1.0	μA
			$T_J = 125^\circ\text{C}$		-10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	-1.0		-3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.0\text{ A}$		70	95	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		120	165	
Forward Transconductance	g_{FS}	$V_{DS} = -1.5\text{ V}, I_D = -3.0\text{ A}$		5.0		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -10\text{ V}$		280	360	pF
Output Capacitance	C_{OSS}			80	110	
Reverse Transfer Capacitance	C_{RSS}			52	80	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -3.0\text{ A}$		2.8	4.2	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.4		
Gate-to-Source Charge	Q_{GS}			1.1		
Gate-to-Drain Charge	Q_{GD}			1.1		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DS} = -10\text{ V}, I_D = -3.0\text{ A}$		5.8	8.8	nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -10\text{ V}, V_{DS} = -10\text{ V}, I_D = -1.0\text{ A}, R_G = 6.0\ \Omega$		7.2	15	ns
Rise Time	t_r			12	24	
Turn-Off Delay Time	$t_{d(OFF)}$			18	36	
Fall Time	t_f			2.6	6.0	

DRAIN-TO-SOURCE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_D = -1.3\text{ A}$	$T_J = 25^\circ\text{C}$		-0.8	-1.0	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = -1.3\text{ A}$		12.8		ns	
Charge Time	t_a			10			
Discharge Time	t_b			2.8			
Reverse Recovery Time	Q_{RR}			7.4			nC

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Maximum Instantaneous Forward Voltage	V_F	$I_F = 1.0\text{ A}$	$T_J = 25^\circ\text{C}$		0.43	0.50	V
			$T_J = 125^\circ\text{C}$		0.35	0.39	
		$I_F = 2.0\text{ A}$	$T_J = 25^\circ\text{C}$		0.5	0.58	
			$T_J = 125^\circ\text{C}$		0.45	0.53	
Maximum Instantaneous Reverse Current	I_R	$V_R = 10\text{ V}$	$T_J = 25^\circ\text{C}$		0.001	0.02	mA
			$T_J = 125^\circ\text{C}$		1.2	14	
		$V_R = 20\text{ V}$	$T_J = 25^\circ\text{C}$		0.004	0.05	
			$T_J = 125^\circ\text{C}$		2.0	18	

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

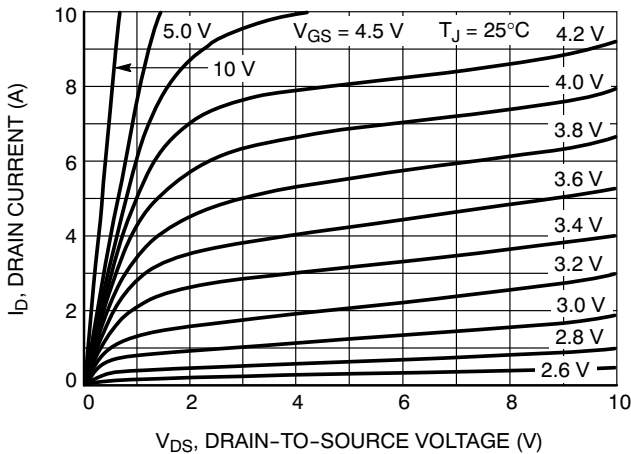


Figure 1. On-Region Characteristics

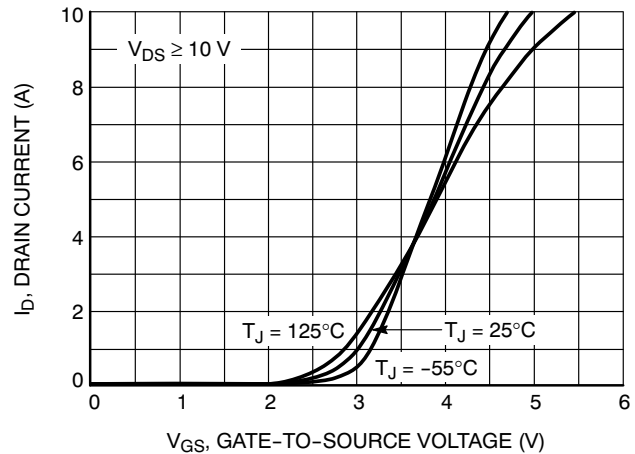


Figure 2. Transfer Characteristics

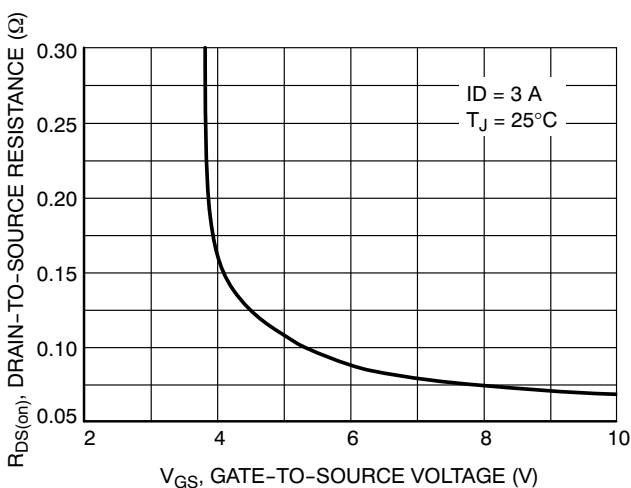


Figure 3. On-Resistance vs. Gate Voltage

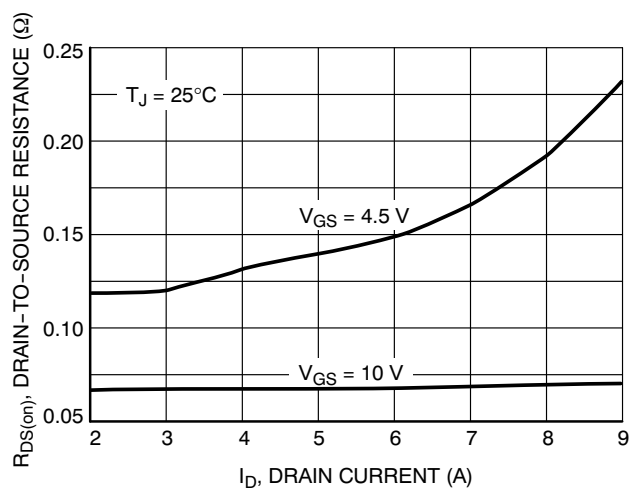


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

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TYPICAL CHARACTERISTICS

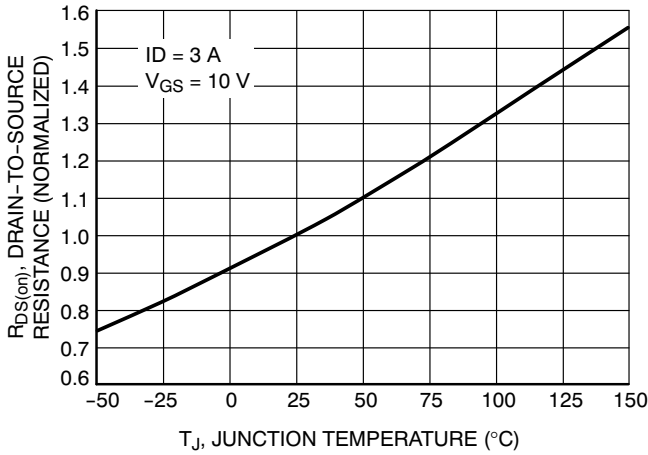


Figure 5. On-Resistance Variation with Temperature

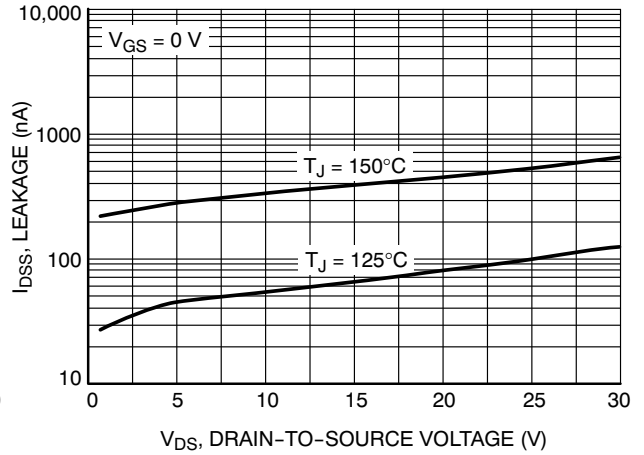


Figure 6. Drain-to-Source Leakage Current vs. Voltage

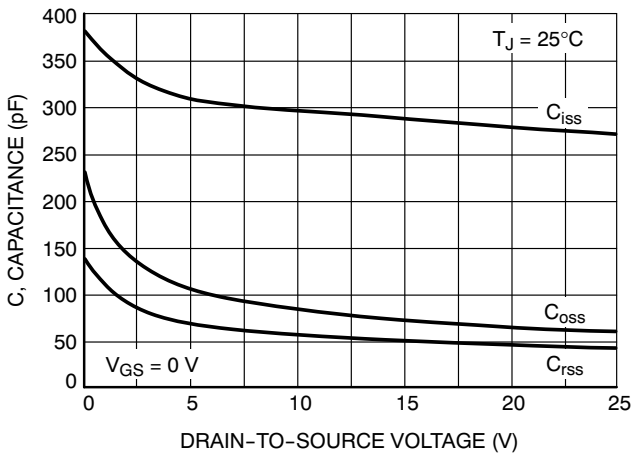


Figure 7. Capacitance Variation

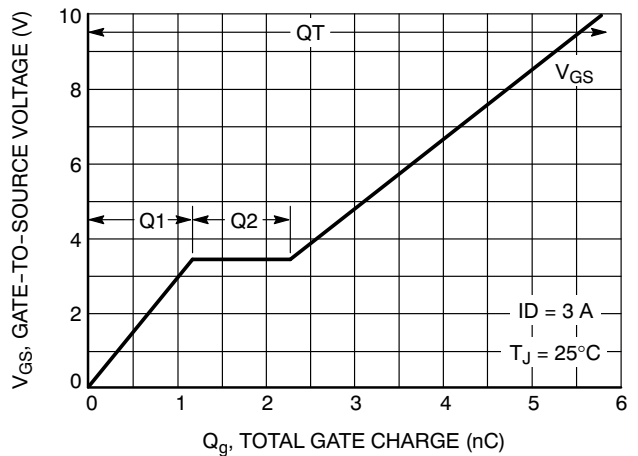


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

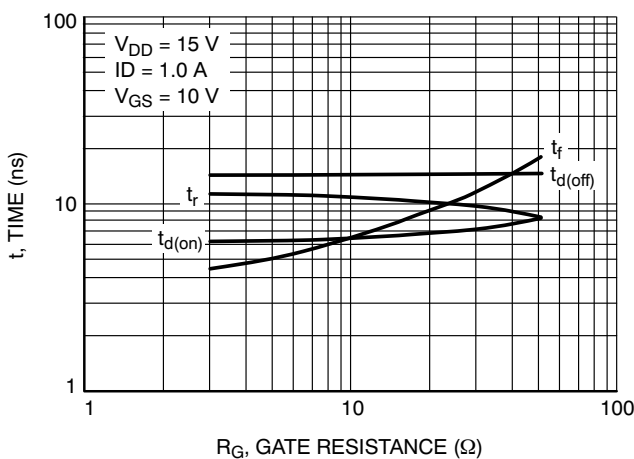


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

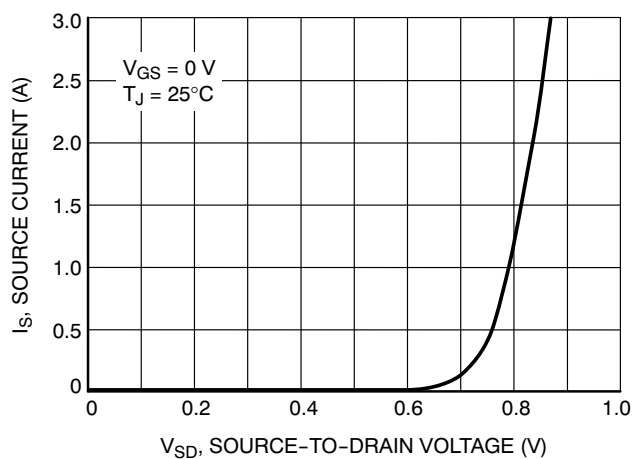


Figure 10. Diode Forward Voltage vs. Current

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TYPICAL CHARACTERISTICS

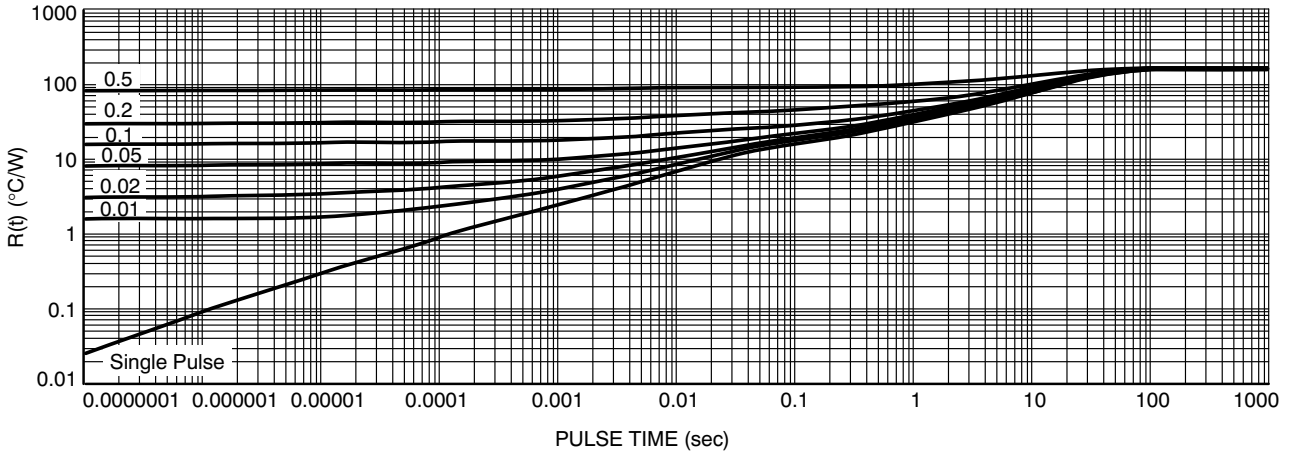


Figure 11. Thermal Response - $R_{\theta JA}$ at Steady State (min pad)

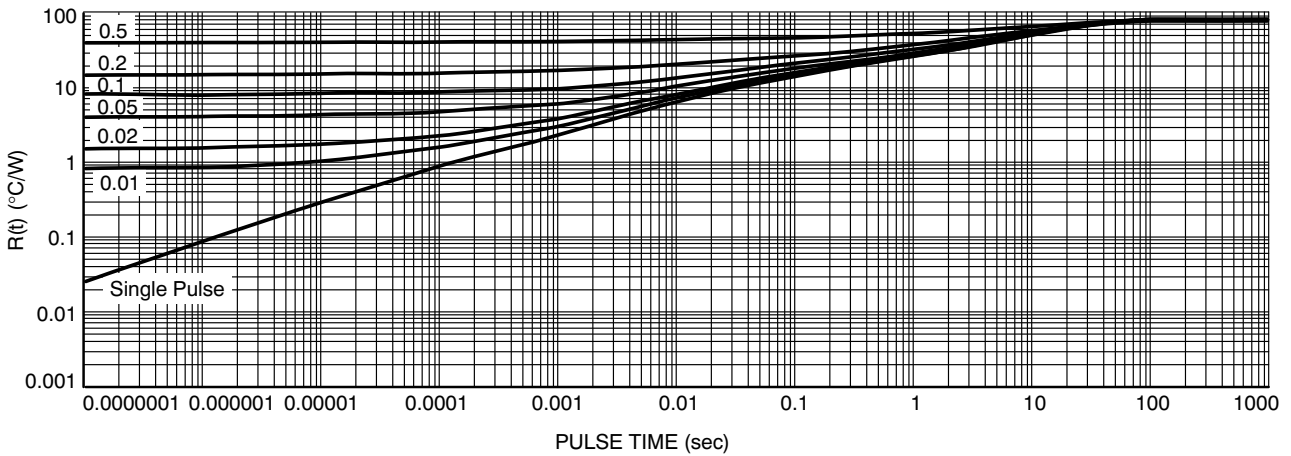


Figure 12. Thermal Response - $R_{\theta JA}$ at Steady State (1 inch sq pad)

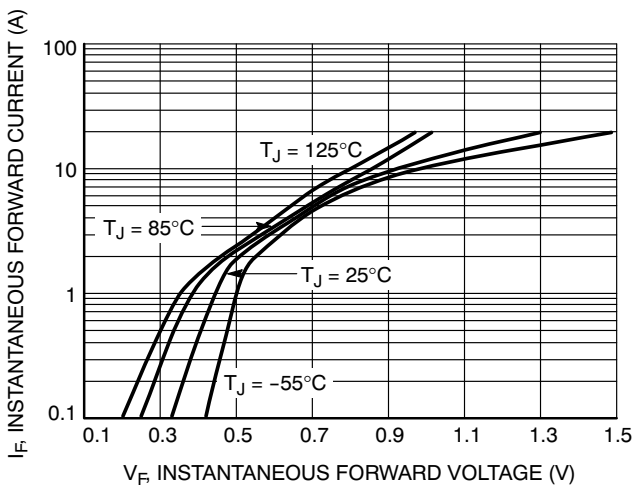


Figure 13. Typical Forward Voltage

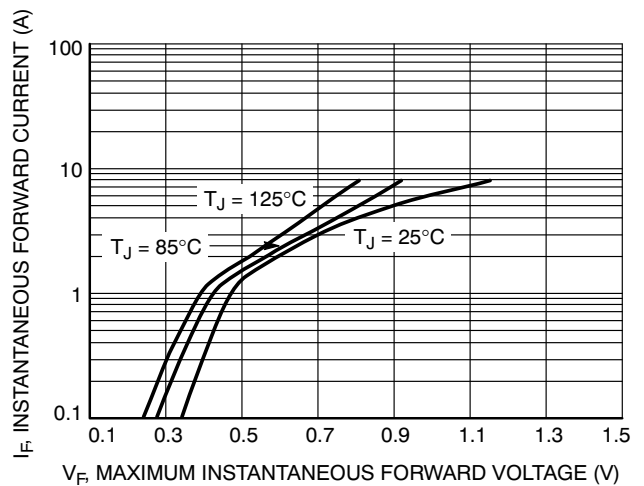


Figure 14. Maximum Forward Voltage

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TYPICAL CHARACTERISTICS

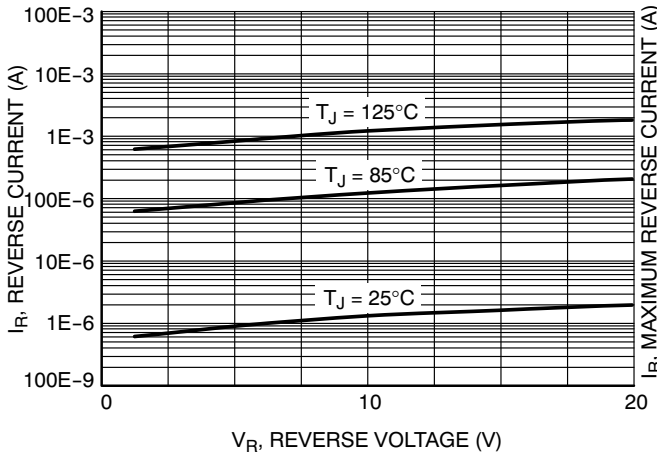


Figure 15. Typical Reverse Current

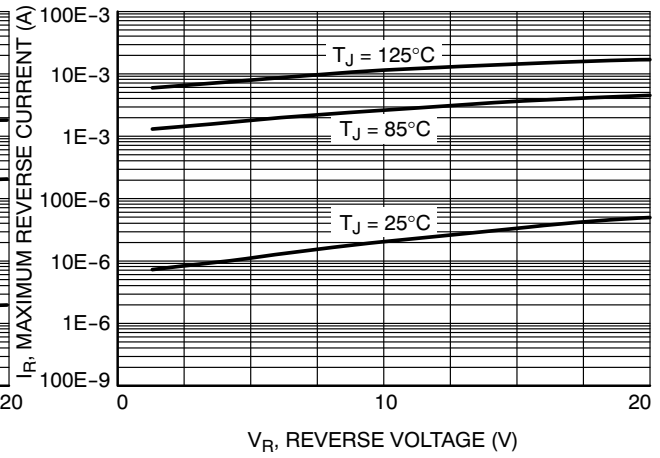


Figure 16. Maximum Reverse Current

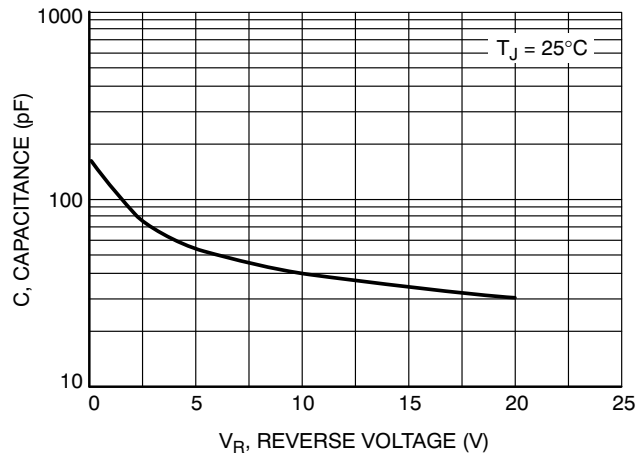
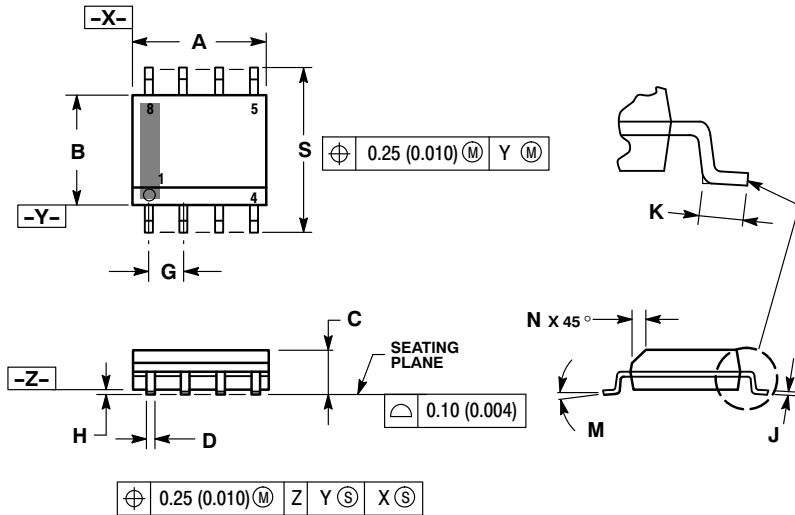


Figure 17. Capacitance

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PACKAGE DIMENSIONS

SOIC-8 NB
CASE 751-07
ISSUE AH

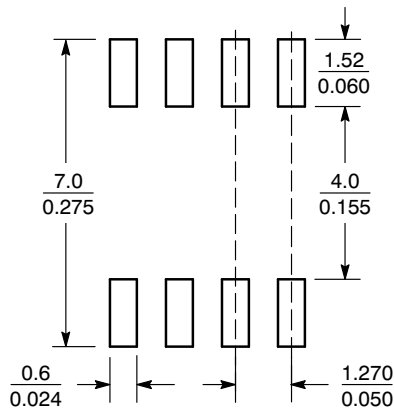


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



SCALE 6:1 (mm/inches)

STYLE 18:

- PIN 1. ANODE
- 2. ANODE
- 3. SOURCE
- 4. GATE
- 5. DRAIN
- 6. DRAIN
- 7. CATHODE
- 8. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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